



SSC8130GN4

N-Channel Enhanced MOSFET

➤ Features

VDS	VGS	RDSON Typ.	ID
30V	±20V	5mR@10V	55A
		7.6mR@4V5	

➤ Description

This device is N-Channel enhancement MOSFET. Uses advanced trench technology and design to provide excellent RDSON with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit.

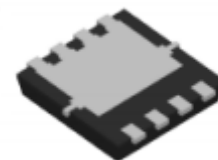
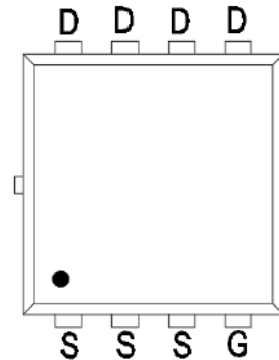
➤ Applications

- DC/DC converters
- Power supplies
- Motor Drive Control
- Synchronous rectification

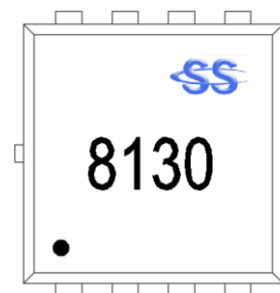
➤ Ordering Information

Device	Package	Shipping
SSC8130GN4	PDFN3.3X3.3	5000/Reel

➤ Pin configuration



Bottom View



Marking



➤ **Absolute Maximum Ratings**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Unit	
V_{DSS}	Drain-to-Source Voltage	30	V	
V_{GSS}	Gate-to-Source Voltage	± 20	V	
I_D	Continuous Drain Current ^d	$T_C=25^{\circ}\text{C}$	55	A
		$T_C=100^{\circ}\text{C}$	32	
I_{DSM}	Continuous Drain Current ^a	$T_A=25^{\circ}\text{C}$	26	A
		$T_A=70^{\circ}\text{C}$	17	
I_{DM}	Pulsed Drain Current ^b	220	A	
P_D	Power Dissipation ^c	$T_C=25^{\circ}\text{C}$	29	W
		$T_C=100^{\circ}\text{C}$	11.6	
P_{DSM}	Power Dissipation ^a	$T_A=25^{\circ}\text{C}$	3.6	W
		$T_A=70^{\circ}\text{C}$	2.3	
I_{AS}	Avalanche Current ^b L=0.5mH Single Pulse	25	A	
E_{AS}	Avalanche Energy ^b L=0.5mH Single Pulse	156	mJ	
T_J	Operation junction temperature	-55~150	$^{\circ}\text{C}$	
T_{STG}	Storage temperature range	-55~150		

➤ **Thermal Resistance Ratings**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance ^a	35	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Junction-to-Case Thermal Resistance	4.3	

Note:

- The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz.copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user is specific board design. The power dissipation is based on the $t \leq 10\text{s}$ thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation P_D is based on $T_{J(\text{MAX})}=150^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.
- The maximum current rating is package limited.

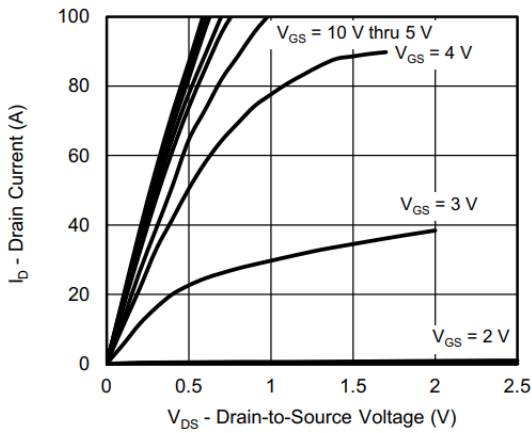


➤ **Electronics Characteristics**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

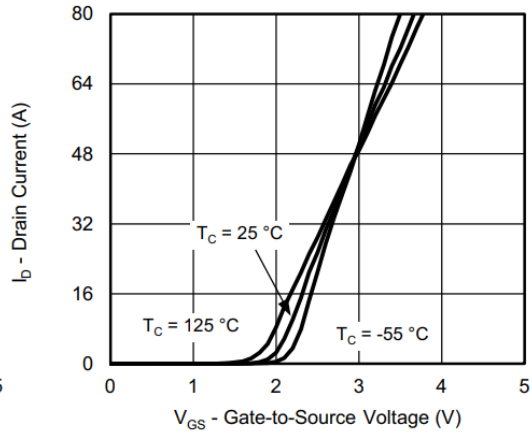
Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.7	3	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V, I_D=20A$		4	5.5	mR
		$V_{GS}=4.5V, I_D=10A$		6	8	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=24V, V_{GS}=0V$			1	μA
I_{GSS}	Gate-Source leak current	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
G_{FS}	Transconductance	$V_{DS}=5V, I_D=10A$		16		S
V_{SD}	Forward Voltage	$V_{GS}=0V, I_S=10A$		0.8	1.3	V
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V,$ $f=1MHz$		2350		pF
C_{oss}	Output Capacitance			280		
C_{rss}	Reverse Transfer Capacitance			260		
$T_{D(ON)}$	Turn-on delay time	$V_{GS}=10V, R_L=3R$ $V_{DS}=15V, R_G=1R$		15		ns
T_r	Rise time			7		
$T_{D(OFF)}$	Turn-off delay time			25		
T_f	Fall time			6		
Q_G	Total Gate Charge	$V_{GS}=10V, V_{DS}=15V$ $I_D=20A$		26		nC
Q_{GS}	Gate Source Charge			12		
Q_{GD}	Gate Drain Charge			5.4		
T_{rr}	Diode Recovery Time	$I_F=10A, di/dt=100A/\mu s$		40		ns
Q_{rr}	Diode Recovery Charge	$I_F=10A, di/dt=100A/\mu s$		55		nC



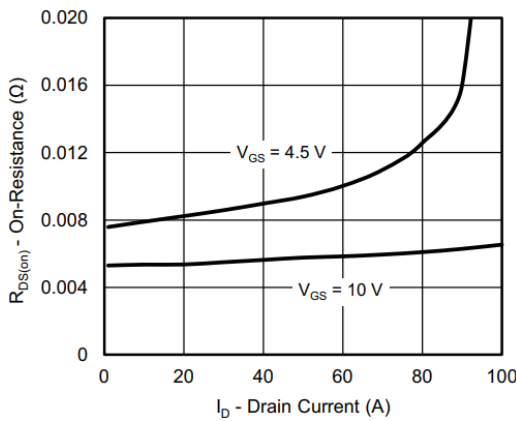
➤ **Typical Characteristics** ($T_A=25^\circ\text{C}$ unless otherwise noted)



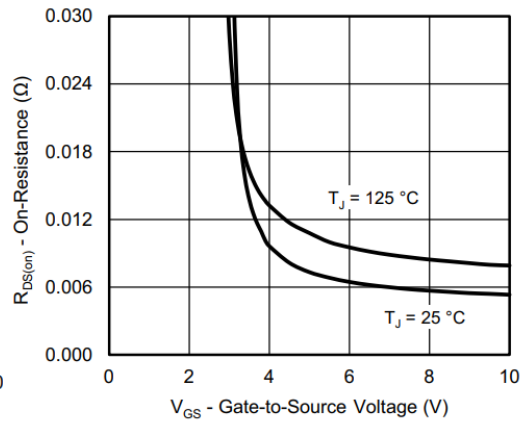
Output Characteristics



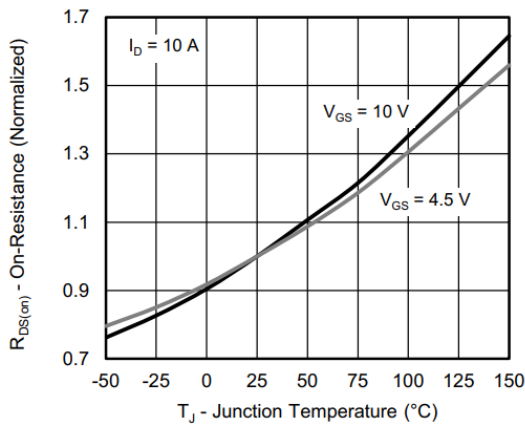
Transfer Characteristics



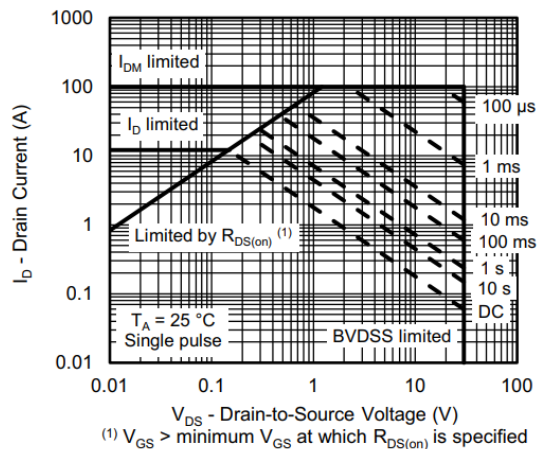
On-Resistance vs. Drain Current



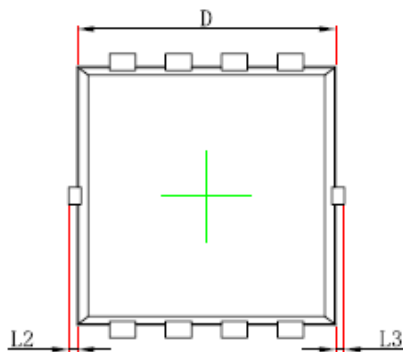
On-Resistance vs. Gate-to-Source Voltage



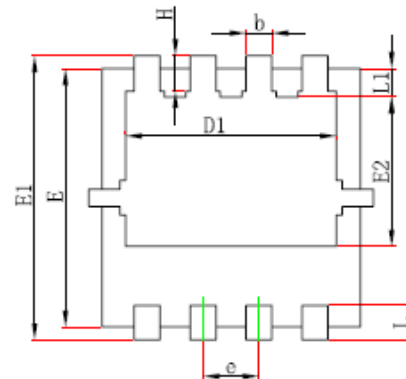
On-Resistance vs. Junction Temperature



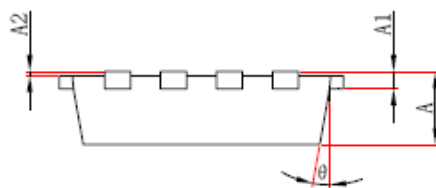
Safe Operating Area

➤ Package Information


Top View
[顶视图]



Bottom View
[背视图]



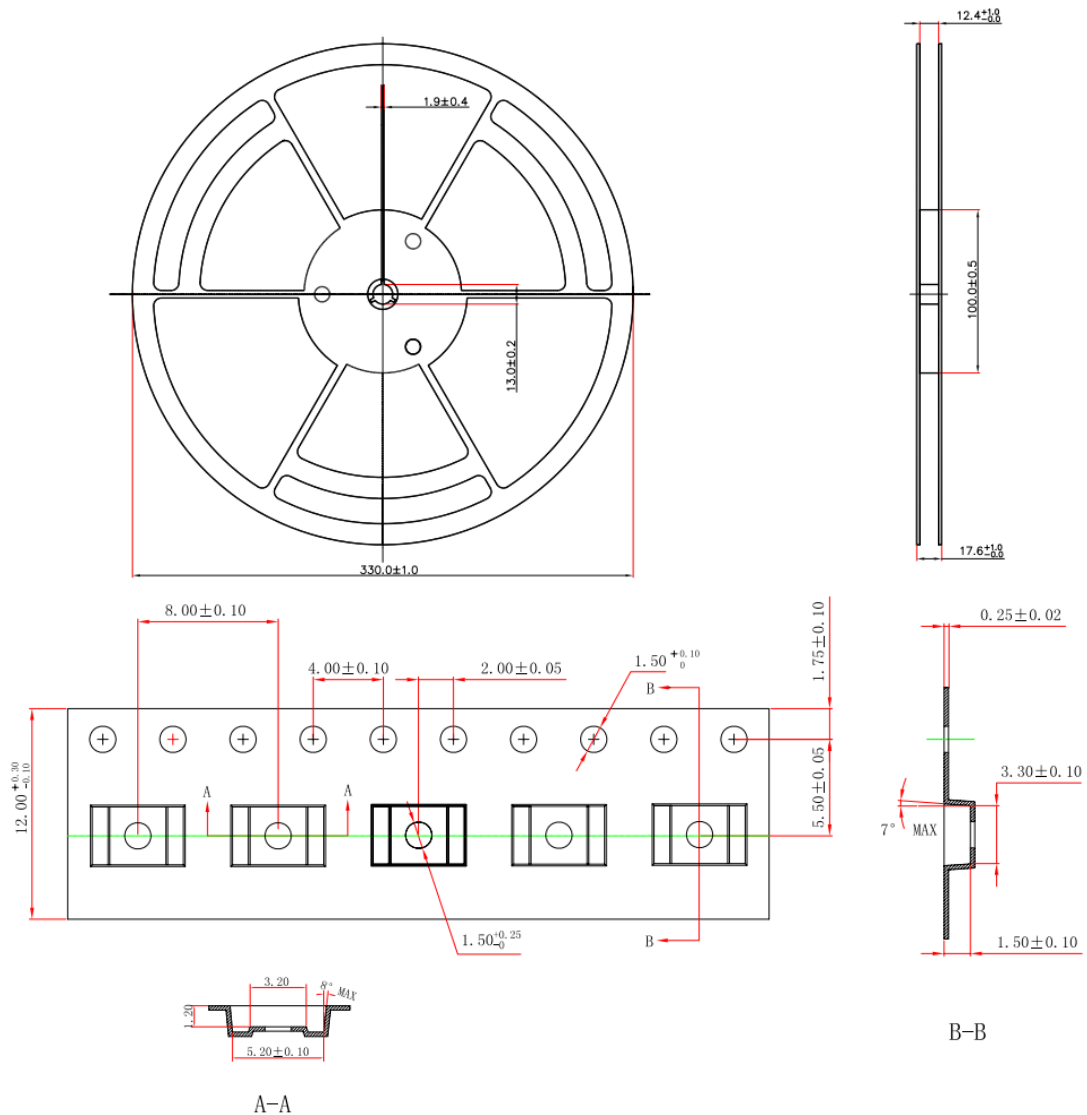
Side View
[侧视图]

Package: PDNF3.3X3.3-8L

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.650	0.850	0.026	0.033
A1	0.152 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	2.900	3.100	0.114	0.122
D1	2.300	2.600	0.091	0.102
E	2.900	3.100	0.114	0.122
E1	3.150	3.450	0.124	0.136
E2	1.535	1.935	0.060	0.076
b	0.200	0.400	0.008	0.016
e	0.550	0.750	0.022	0.030
L	0.300	0.500	0.012	0.020
L1	0.180	0.480	0.007	0.019
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.315	0.515	0.012	0.020
θ	9°	13°	9°	13°



➤ Tape and Reel



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